

Remarks

This is intended as a full and complete response to the Office Action dated August 13, 2003, having a shortened statutory period for response set to expire on November 13, 2003. The Applicant and the Examiner had an informal phone conference on November 4. Patentability of claim 50 was discussed absent any translation of JP 59197127 (*Yamazaki*). However, an agreement was not made. The Applicant renews the request for any translation of the JP 59197127 (*Yamazaki*) obtained by the Examiner. Please reconsider the claims pending in the application for reasons discussed below.

Claims 42-50, 109 and 110 remain pending in the application and are shown above as amended. Claims 42, 45, 46, and 50 are amended to specify that the conductivity decreasing volatile includes two or more components. Claims 42-50, 109 and 110 are rejected. Reconsideration of the rejected claims is requested for reasons presented below.

Claims 42-50, stand rejected under 35 USC § 103(a) as being unpatentable over the Abstract of JP 59197127A (*Yamazaki*) in view of Applicant's admitted prior art. Claims 109-110 stand rejected under 35 USC § 103(a) as being unpatentable over the Abstract of *Yamazaki* as applied to claims 42-50 above, and further in view of Applicant's admitted prior art. Applicants respectfully traverse the rejection of claims 42-50 and 109-110 as amended.

Claims 42-50 and 109-110 as amended specify a conductivity decreasing volatile including two or more components. The *Yamazaki* abstract alone or in combination with any admissions by Applicant do not suggest a combination of components that form the conductivity decreasing volatile. Therefore, absent translation of *Yamazaki*, the Examiner has no basis for finding that the art of record teaches, shows, or suggests introducing a silicon-based volatile into the deposition chamber, introducing into the deposition chamber a conductivity-increasing volatile including one or more components for increasing the conductivity of the amorphous silicon-based film, and introducing into the deposition chamber a conductivity-decreasing volatile including two or more components for decreasing the conductivity of the amorphous silicon-based film,

wherein the conductivity-increasing and conductivity-decreasing volatile are introduced into said deposition chamber at a flow rate ratio between about 1:1 and about 1:1000 conductivity-increasing to conductivity-decreasing volatile; thereby forming said amorphous silicon-based film on said substrate, as recited in claim 42, and claims dependent thereon. Withdrawal of the rejection is respectfully requested.

In conclusion, the references cited by the Examiner, alone or in combination, do not teach, show, or suggest the invention as claimed.

Having addressed all issues set out in the office action, Applicant respectfully submits that the claims are in condition for allowance and respectfully request that the claims be allowed.

Respectfully submitted,



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